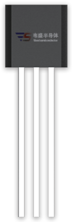
KSA642 TRANSISTOR (PNP)

FEATURES

- General Purpose Amplifier Transistor



TO-92

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSA642	TO-92	Bulk	1000pcs/Bag
KSA642-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.3	A
P_C	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	312	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=- 0.1mA,I_E=0	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-25V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V,I_C=0			-0.1	μA
DC current gain	h_{FE}^*	V_{CE}=-1V, I_C=-50mA	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	I_C=-0.3A,I_B=-30mA			-0.6	V

*Pulse test: pulse width ≤350μs, duty cycle≤ 2.0%.

CLASSIFICATION OF h_{FE}

RANK	O	Y	G
RANGE	70-140	120-240	200-400